

L Number	Hits	Search Text	DB	Time stamp
92	16	5248629.URPN.	USPAT	2003/08/23 13:04
95	6	("5338951" "6027967" "6201276" "6204203" "6303434" "6303455").PN.	USPAT	2003/08/23 13:07
96	2	meta\$1stable with poly\$1silicon and capacitor	USPAT; EPO; JPO	2003/08/23 13:11
97	1	meta\$1stable with poly\$1silicon and phosphor\$3	USPAT; EPO; JPO	2003/08/23 13:12
98	2	meta\$1stable with poly\$1silicon and electrode	USPAT; EPO; JPO	2003/08/23 13:13
99	3	meta\$1stable with poly\$1silicon	USPAT; EPO; JPO	2003/08/23 13:13
100	6	(meta\$1stable meta adj stable) with (poly\$1silicon poly adj silicon)	USPAT; EPO; JPO	2003/08/23 13:14
-	1	(tantalum adj oxy).ti. and park.in.	USPAT; US-PGPUB	2003/08/20 18:25
-	1	tantalum adj oxy.ti. and electrode and deposit\$3 and etch\$3 and dop\$3 and (nitrating nitrifying)	USPAT; US-PGPUB; EPO; JPO	2003/08/20 18:26
-	1	tantalum adj oxy and electrode and deposit\$3 and etch\$3 and dop\$3 and (nitrating nitrifying)	USPAT; US-PGPUB; EPO; JPO	2003/08/20 18:27
-	12	tantalum and capacitor and electrode and deposit\$3 and etch\$3 and dop\$3 and (nitrating nitrifying)	USPAT; EPO; JPO	2003/08/20 18:31
-	287	tantalum with capacitor and electrode and deposit\$3 and etch\$3 and dop\$3 and nitride with film	USPAT; EPO; JPO	2003/08/20 18:42
-	232	(tantalum with capacitor and electrode and deposit\$3 and etch\$3 and dop\$3 and nitride with film) and silicon and chemical	USPAT; EPO; JPO	2003/08/20 18:32
-	79	((tantalum with capacitor and electrode and deposit\$3 and etch\$3 and dop\$3 and nitride with film) and silicon and chemical) and chamber	USPAT; EPO; JPO	2003/08/20 18:41
-	1	5631188.pn.	USPAT; EPO; JPO	2003/08/20 18:42
-	1	6156608.pn.	USPAT; EPO; JPO	2003/08/20 18:42
-	244	tantalum and capacitor.ti. and electrode and deposit\$3 and etch\$3 and dop\$3 and nitride with film	USPAT; EPO; JPO	2003/08/20 18:43
-	48	(tantalum and capacitor.ti. and electrode and deposit\$3 and etch\$3 and dop\$3 and nitride with film) and silicon and chamber	USPAT; EPO; JPO	2003/08/20 18:49
-	0	metastable with poly with silicon and doping and depositing and electrode	USPAT; EPO; JPO	2003/08/20 18:50
-	1886	gas with silicon and doping and depositing and electrode	USPAT; EPO; JPO	2003/08/20 18:50
-	364	(gas with silicon and doping and depositing and electrode) and nitride adj1 (film layer) and chamber	USPAT; EPO; JPO	2003/08/20 18:51
-	102	((gas with silicon and doping and depositing and electrode) and nitride adj1 (film layer) and chamber) and etch\$3 and tantalum	USPAT; EPO; JPO	2003/08/20 18:52
-	68	((gas with silicon and doping and depositing and electrode) and nitride adj1 (film layer) and chamber) and etch\$3 and tantalum) and chemical adj vapor\$3	USPAT; EPO; JPO	2003/08/20 18:52
-	0	((((gas with silicon and doping and depositing and electrode) and nitride adj1 (film layer) and chamber) and etch\$3 and tantalum) and chemical adj vapor\$3) and phosphor	USPAT; EPO; JPO	2003/08/20 18:55

-	67	((((gas with silicon and doping and depositing and electrode) and nitride adj1 (film layer) and chamber) and etch\$3 and tantalum) and chemical adj vapor\$3) and semiconductor	USPAT; EPO; JPO	2003/08/20 18:55
-	6	(((((gas with silicon and doping and depositing and electrode) and nitride adj1 (film layer) and chamber) and etch\$3 and tantalum) and chemical adj vapor\$3) and semiconductor) and capacitor.ti.	USPAT; EPO; JPO	2003/08/20 18:56
-	0	tantalum adj oxy adj nitride adj capacitor	USPAT; EPO; JPO	2003/08/21 10:15
-	1	tantalum adj1 oxy adj1 nitride adj1 capacitor	USPAT; US-PGPUB; EPO; JPO	2003/08/21 10:15
-	319	tantalum with capacitor.ti.	USPAT; US-PGPUB; EPO; JPO	2003/08/21 10:16
-	23	(tantalum with capacitor.ti.) and etch\$3 and chemical adj1 vapor\$3	USPAT; US-PGPUB; EPO; JPO	2003/08/21 10:25
-	2	TANTALUM adj1 OXYNITRIDE adj1 CAPACITOR	USPAT; US-PGPUB; EPO; JPO	2003/08/21 10:29
-	42	TANTALUM with OXYNITRIDE with CAPACITOR	USPAT; EPO; JPO	2003/08/21 10:38
-	1	6037205.pn.	USPAT; EPO; JPO	2003/08/21 10:39
-	1	5910880.pn.	USPAT; EPO; JPO	2003/08/21 10:39
-	1	5677015.pn.	USPAT; EPO; JPO	2003/08/21 10:39
-	1	5352623.pn.	USPAT; EPO; JPO	2003/08/21 10:39
-	124	capacitor.ti. and tantalum and dop\$3 with silicon and gas\$3 and etch\$3 and deposit\$3 and nitride adj (film layer) and electrode and chemical adj vapor\$4	USPAT; EPO; JPO	2003/08/21 16:10
-	30	capacitor and poly\$1crystalline with grow\$3 and tantalum and dop\$3 with silicon and gas\$3 and etch\$3 and deposit\$3 and nitride adj (film layer) and electrode and chemical adj vapor\$4	USPAT; EPO; JPO	2003/08/21 16:50
-	10	capacitor.ti. and poly\$1crystalline with grow\$3 and tantalum and dop\$3 with silicon and gas\$3 and etch\$3 and deposit\$3 and nitride adj (film layer) and electrode and chemical adj vapor\$4	USPAT; EPO; JPO	2003/08/21 16:50
-	183	capacitor and (taon tantalum near2 nitride) and electrode and nitride adj (film layer) and deposit\$3 and etch\$3 and gas\$4 and chemical with vapor\$4	USPAT; EPO; JPO	2003/08/22 10:18
-	101	(capacitor and (taon tantalum near2 nitride) and electrode and nitride adj (film layer) and deposit\$3 and etch\$3 and gas\$4 and chemical with vapor\$4) and chamber	USPAT; EPO; JPO	2003/08/22 10:18
-	9	capacitor and taon and silicon and electrode and nitride adj (film layer) and deposit\$3 and etch\$3 and gas\$4 and chemical with vapor\$4 and chamber	USPAT; EPO; JPO	2003/08/22 13:01
-	16	("4891684" "5070384" "5216572" "5668040" "5712813" "6046489" "6060736" "6078493" "6180481" "6215646" "6222219" "6287910" "6303958" "6306667" "6407419" "6437391" "2001/0014498" "2002/0000598").PN.	USPAT	2003/08/22 10:22

-	11	capacitor and taon and silicon and electrode and nitride adj (film layer) and deposit\$3 and etch\$3 and gas\$4 and chemical with vapor\$4	USPAT; EPO; JPO	2003/08/22 13:16
-	2	capacitor and taon and mps and silicon and electrode and nitride adj (film layer) and etch\$3 and gas\$4 and chemical with vapor\$4	USPAT; EPO; JPO	2003/08/22 13:17
-	2	capacitor and taon and mps and silicon and electrode and nitride adj (film layer) and etch\$3 and gas\$4	USPAT; EPO; JPO	2003/08/22 13:18
-	3	capacitor and taon and mps and silicon and electrode and nitride adj (film layer)and gas\$4	USPAT; EPO; JPO	2003/08/22 13:34
-	18	capacitor and taon and silicon and electrode and nitride adj (film layer)and gas\$4	USPAT; EPO; JPO	2003/08/22 13:35
-	5	taon and (p ph\$1 phosphor) and capacitor and gas\$4	USPAT; EPO; JPO	2003/08/22 18:23
-	3	taon and (p phosphor) and capacitor and gas\$4	USPAT; EPO; JPO	2003/08/22 18:24
-	5	taon and (p phosphor\$3) and capacitor and gas\$4	USPAT; EPO; JPO	2003/08/22 18:46
-	7	taon and tantalum with ethylate and capacitor and gas\$4	USPAT; EPO; JPO	2003/08/22 18:47